

Claims

1. Electronic high frequency switch with a field effect transistor (T) as the switching element, whose  
5 switching condition is controlled via the gate voltage (U), characterised in that the size of the gate voltage (U) is switchable, depending on the desired linearity or switching speed between at least two values (-5.5V and -8V).

2. High frequency switch according to claim 1,  
10 characterised in that the changeover device (S) for the gate voltage (U) is coupled to a correction device (K) in which, for the different gate voltage values, corresponding different correction values for additional high frequency properties of the high frequency switch (transmission or  
15 reflection) are stored which, depending on the gate voltage chosen, are used for correcting these additional high frequency properties of the high frequency switch.

3. Attenuator with a plurality of electronic high frequency switches according to claim 1 or 2, characterised  
20 in that the size of the gate voltage (U) of at least some of the high frequency switches is switchable between at least two values.

4. Attenuator according to claim 3, with a switchable attenuation member (D) connected on the line side, which is  
25 controllable with a correction device (K) in which, depending on the frequency (f) of the high frequency signal fed to the attenuator (E), correction values for compensating for the frequency-dependent junction loss of the electronic high frequency switch are stored,  
30 characterised in that in the correction device (K), different frequency response correction values are stored for the different gate voltage values of the high frequency switches and that the changeover device (S) for the gate

voltage is coupled to this correction device (K) such that, depending on the selected size of the gate voltage, the respective associated frequency response correction values for controlling the attenuation member (D) connected on the  
5 line side are used.

New claims

1. Electronic high frequency switch with a field effect transistor (T) as the switching element, whose  
5 switching condition is controlled via the gate voltage (U) fed from a gate voltage source (U1, U2, U3, U4) and is controlled by means of a control circuit (A) between a switching on value and a switching off value, characterised in that the size of the gate voltage fed from the gate  
10 voltage source (U1, U2, U3, U4) is selectable by a changeover device (S) depending on the desired linearity or switching speed (for example, -5V or -8V).

2. High frequency switch according to claim 1, characterised in that the changeover device (S) for the  
15 gate voltage (U) is coupled to a correction device (K) in which, for the different gate voltage values, corresponding different correction values for additional high frequency properties of the high frequency switch (transmission or reflection) are stored which, depending on the gate voltage  
20 chosen, are used for correcting these additional high frequency properties of the high frequency switch.

3. Attenuator with a plurality of electronic high frequency switches according to claim 1 or 2, characterised in that the size of the gate voltage (U) of at least some  
25 of the high frequency switches is switchable between at least two values.

4. Attenuator according to claim 3, with a switchable attenuation member (D) connected on the line side, which is controllable with a correction device (K) in which,  
30 depending on the frequency (f) of the high frequency signal fed to the attenuator (E), correction values for compensating for the frequency-dependent junction loss of the electronic high frequency switch are stored,

characterised in that in the correction device (K),  
different frequency response correction values are stored  
for the different gate voltage values of the high frequency  
switches and that the changeover device (S) for the gate  
5 voltage is coupled to this correction device (K) such that,  
depending on the selected size of the gate voltage, the  
respective associated frequency response correction values  
for controlling the attenuation member (D) connected on the  
line side are used.